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**THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of: **Yoshihisa IBA**

Patent No.: **7,196,003**

Issued: **March 27, 2007**

For: **METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE**

Attorney Docket Number: **042075**  
Customer Number: **38834**

**REQUEST FOR CERTIFICATE OF CORRECTION**

**Mail Stop: COC**

Commissioner for Patents

January 10, 2008

P. O. Box 1450

Alexandria, VA 22313-1450

Sir:

The undersigned requests that a Certificate of Correction be issued for the above-identified patent as indicated on the attached Form PTO-1050.

This request is being made in order to correct Claims. Please delete the paragraphs beginning at column 6, line 64 and column 7, line 1, and insert the paragraph presented on Form PTO-1050. (See Amendment under 37 C.F.R. §1.111 filed on September 5, 2006). It is respectfully submitted that no new matter has been added.

Because this error is a Patent and Trademark Office printing error, it is respectfully submitted that no fee is required.

If any fees are required in connection with this paper, please charge Deposit Account No. 50-2866.

Respectfully submitted,

**WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP**

  
Darrin A. Auito  
Attorney for Applicant  
Registration No. 56,024  
Telephone: (202) 822-1100  
Facsimile: (202) 822-1111

**Certificate**

**JAN 14 2008**

**of Correction**

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Enclosures: Form PTO-1050

**UNITED STATES PATENT AND TRADEMARK OFFICE**  
**CERTIFICATE OF CORRECTION**

PATENT NO. **7,196,003**

DATED: **March 27, 2007**

INVENTOR(S): **Yoshihisa IBA**

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

**On Claims**

Please delete the paragraphs beginning at column 6, line 64 and column 7, line 1, and insert the following paragraph (See Amendment under 37 C.F.R. &1.11 filed on September 5, 2006).

--The etching of SiO<sub>2</sub> film 6 is performed using the plasma etching device, for example, under the condition of 20 sccm of C<sub>4</sub>F<sub>8</sub>, 15 sccm of O<sub>2</sub>, 200 sccm of Ar, 4.00 Pa (30 mTorr) of pressure, and 1500 W of RF source power.--

MAILING ADDRESS OF SENDER:  
**Westerman, Hattori, Daniels & Adrian, LLP**  
**1250 Connecticut Avenue NW - Suite 700**  
**Washington, DC 20036-2657**

PATENT NO. **7,196,003**

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